

# **MOSFET** - N-Channel, **SOT-23**

300 mA, 20 V

## MMBF0201NL, MVMBF0201NL

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### **Features**

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- MVMBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- These Devices are Pb-Free and are RoHS Compliant

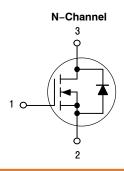
#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
$ \begin{array}{ll} \text{Drain Current} \\ - \text{ Continuous } @ \text{ T}_A = 25^{\circ}\text{C} \\ - \text{ Continuous } @ \text{ T}_A = 70^{\circ}\text{C} \\ - \text{ Pulsed Drain Current } (t_p \leq 10 \mu\text{s}) \end{array} $	I <sub>D</sub> I <sub>D</sub> I <sub>DM</sub>	300 240 750	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C	P <sub>D</sub>	225	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

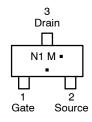
## 300 mAMPS – 20 VOLTS $R_{DS(on)} = 1 \Omega$



#### MARKING DIAGRAM AND PIN ASSIGNMENT



SOT-23 CASE 318 STYLE 21



N1 = Specific Device Code
M = Date Code\*
= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBF0201NLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MVMBF0201NLT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MMBF0201NL, MVMBF0201NL

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Chara	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μA)		V <sub>(BR)DSS</sub>	20	_	-	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 16 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 16 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)		I <sub>DSS</sub>	_ _	_ _	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> =	I <sub>GSS</sub>	_	-	±100	nAdc	
ON CHARACTERISTICS (Note 1)		•	•			
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 250 \mu Adc)$	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc	
$ \begin{array}{l} \text{Static Drain-to-Source On-Resistan} \\ \text{(V}_{\text{GS}} = 10 \text{ Vdc, I}_{\text{D}} = 300 \text{ mAdc)} \\ \text{(V}_{\text{GS}} = 4.5 \text{ Vdc, I}_{\text{D}} = 100 \text{ mAdc)} \end{array} $	r <sub>DS(on)</sub>	- -	0.75 1.0	1.0 1.4	Ω	
Forward Transconductance (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 200 mAdc)		9FS	-	450	-	mMhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>iss</sub>	-	45	_	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>oss</sub>	-	25	-	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 V)	C <sub>rss</sub>	-	5.0	_	
SWITCHING CHARACTERISTICS (	Note 2)					
Turn-On Delay Time		t <sub>d(on)</sub>	-	2.5	_	ns
Rise Time	$(V_{DD} = 15 \text{ Vdc}, I_D = 300 \text{ mAdc},$	t <sub>r</sub>	-	2.5	-	
Turn-Off Delay Time	$R_L = 50 \Omega$ )	t <sub>d(off)</sub>	-	15	_	
Fall Time		t <sub>f</sub>	-	0.8	-	
Gate Charge (See Figure 5)		Q <sub>T</sub>	_	1400	_	рС
SOURCE-DRAIN DIODE CHARACT	TERISTICS					
Continuous Current	I <sub>S</sub>	-	-	0.3	А	
Pulsed Current	I <sub>SM</sub>	-	-	0.75		
Forward Voltage (Note 2)		$V_{SD}$	-	0.85	-	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

2. Switching characteristics are independent of operating junction temperature.

### MMBF0201NL, MVMBF0201NL

#### TYPICAL ELECTRICAL CHARACTERISTICS

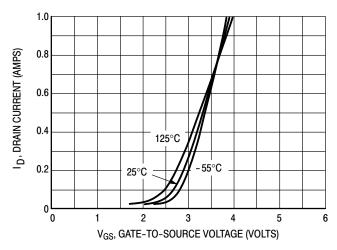
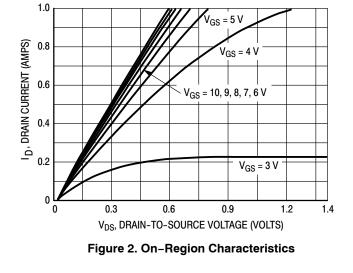


Figure 1. Transfer Characteristics



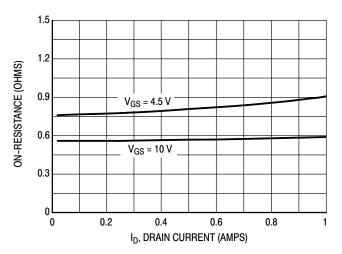


Figure 3. On-Resistance versus Drain Current

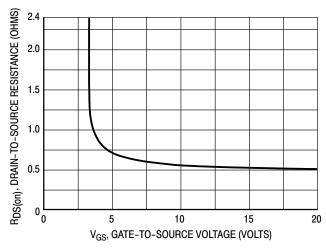


Figure 4. On-Resistance versus Gate-to-Source Voltage

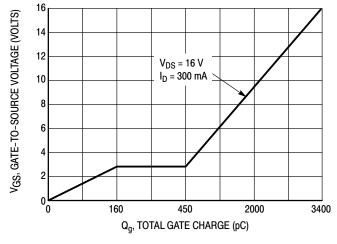


Figure 5. Gate Charge

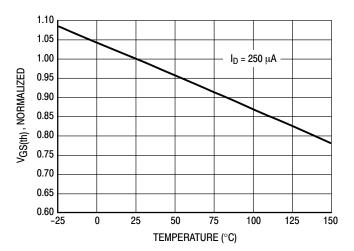


Figure 6. Threshold Voltage Variance Over Temperature

## MMBF0201NL, MVMBF0201NL

#### TYPICAL ELECTRICAL CHARACTERISTICS

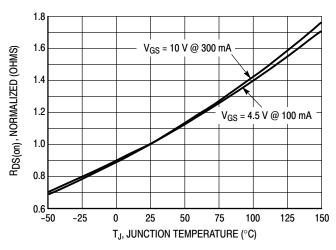


Figure 7. On-Resistance versus Junction Temperature

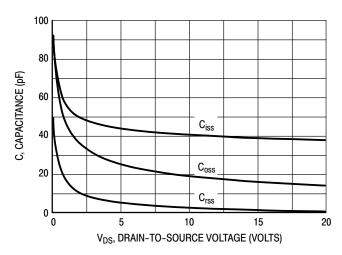


Figure 8. Capacitance

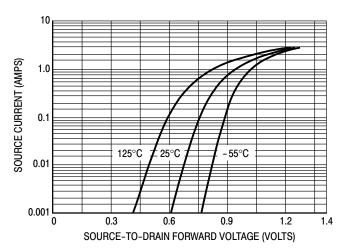


Figure 9. Source-to-Drain Forward Voltage versus Continuous Current (I<sub>S</sub>)

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

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#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

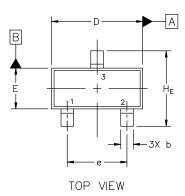
2.04

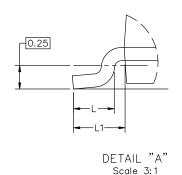
0.55

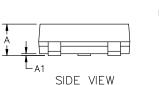
0.69

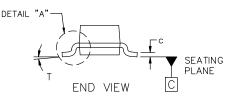
2.64

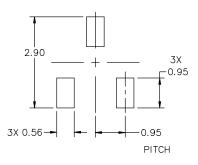
10°











#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODI	
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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